











SN74CBTLV3257

ZHCSIJ4M - DECEMBER 1997 - REVISED JULY 2018

# SN74CBTLV3257 低电压、4 位、2 选 1 FET 多路复用器/多路解复用器

# 特性

- 两个端口间使用 5Ω 开关连接
- 数据 I/O 端口上的轨至轨开关
- I<sub>off</sub> 支持局部关断模式运行
- 闩锁性能超出 JESD 78 II 类规范要求的 100mA
- 静电放电 (ESD) 保护性能超过 JESD 22 规范的要 求
  - 2000V 人体放电模型 (A114-A)
  - 200V 机器模型 (A115-A)

# 2 应用范围

- 物联网
- 无线耳机
- 电视机
- 4 位总线多路复用和多路解复用

# 3 说明

SN74CBTLV3257 器件是一款 4 位 2 选 1 高速 FET 多路复用器/多路解复用器。此开关具有低通态电阻, 可以在最短传播延迟情况下建立连接。

选择 (S) 输入控制数据流。当输出使能 (OE) 输入为高 电平时,FET 多路复用器/多路解复用器被禁用。

该器件完全 适用于 使用 Ioff 的局部掉电应用。Ioff 特性 确保在关断时防止损坏电流通过器件回流。该器件可在 关断时提供隔离。

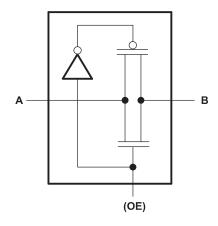
为了确保加电或断电期间的高阻抗状态, OE 应通过一 个上拉电阻器被连接至 Vcc; 该电阻器的最小值由驱动 器的电流吸入能力来决定。

#### 器件信息(1)

器件型号	封装	封装尺寸 (标称值)
SN74CBTLV3257DBQ	SSOP (16)	4.90mm × 3.90mm
SN74CBTLV3257PW	TSSOP (16)	5.00mm × 4.40mm
SN74CBTLV3257DGV	TVSOP (16)	3.60mm × 4.40mm
SN74CBTLV3257D	SOIC (16)	9.90mm x 3.91mm
SN74CBTLV3257RGY	VQFN (16)	4.00mm × 3.50mm
SN74CBTLV3257RSV	UQFN (16)	2.60mm x 1.80mm

(1) 如需了解所有可用封装,请参阅产品说明书末尾的可订购产品 附录。

#### 简化原理图(每个 FET 开关)





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t	已添加 将 TSSOP (16) 添加到器件信息 表				1
A	Added Junction temperature, T <sub>J</sub> in <i>Absolute Maximu</i>	m Ratings.			5
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,	已添加 引脚配置和功能 部分, ESD 额定值 表, 特性	说明 部分	、器化	件功能模式、应用和实施 部分、电源相关建议 部	部
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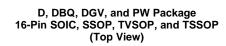
# Changes from Revision I (October 2003) to Revision J

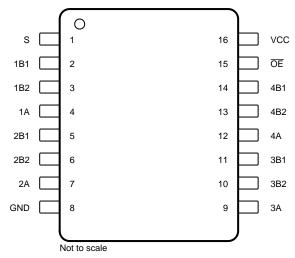
• 添加了 QFN 订购信息和封装引脚布局....... 1

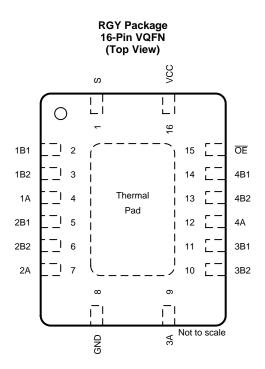
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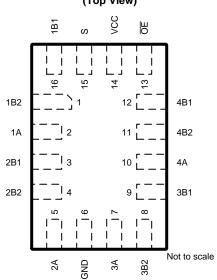
# 5 Pin Configuration and Functions







#### RSV Package 16-Pin UQFN (Top View)





# **Pin Functions**

PIN				
NAME	SOIC, SSOP, TVSOP, TSSOP, VQFN	UQFN	I/O	DESCRIPTION
1A	4	2	I/O	Channel 1 out/in common
1B1	2	16	I/O	Channel 1 in/out 1
1B2	3	1	I/O	Channel 1 in/out 2
2A	7	5	I/O	Channel 2 out/in common
2B1	5	3	I/O	Channel 2 in/out 1
2B2	6	4	I/O	Channel 2 in/out 2
ЗА	9	7	I/O	Channel 3 out/in common
3B1	11	9	I/O	Channel 3 in/out 1
3B2	10	8	I/O	Channel 3 in/out 2
4A	12	10	I/O	Channel 4 out/in common
4B1	14	12	I/O	Channel 4 in/out 1
4B2	13	11	I/O	Channel 4 in/out 2
GND	8	6	_	Ground
ŌĒ	15	13	I	Output Enable, active low
S	1	15	I	Select
V <sub>CC</sub>	16	14	_	Power



# 6 Specifications

#### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			MIN	MAX	UNIT
$V_{CC}$	Supply voltage		-0.5	4.6	V
VI	Input voltage <sup>(2)</sup>		-0.5	4.6	V
	Continuous channel current			128	mA
I <sub>IK</sub>	Input clamp current	V <sub>I/O</sub> < 0		<b>-</b> 50	mA
TJ	Junction temperature			150	°C
T <sub>stg</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

### 6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	2000	٧

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
$V_{CC}$	Supply voltage		2.3	3.6	V
V High level central input voltage	V <sub>CC</sub> = 2.3 V to 2.7 V	1.7		\/	
V <sub>IH</sub>	High-level control input voltage	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2		V
V	Low-level control input voltage	V <sub>CC</sub> = 2.3 V to 2.7 V		0.7	\/
V <sub>IL</sub>		V <sub>CC</sub> = 2.7 V to 3.6 V		8.0	] V
$T_A$	Operating free-air temperature		-40	85	°C

All unused control inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. See Implications of Slow or Floating CMOS InputsSCBA004.

#### 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>			SN74CBTLV3257					
			DBQ	DGV	PW	RGY	UNIT	
		16 PINS	16 PINS	16 PINS	16 PINS	16 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	86.7	112.4	123.1	110.9	43.8	°C/W	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	47.8	63.6	48.7	45.8	57.2	°C/W	
$R_{\theta JB}$	Junction-to-board thermal resistance	43.7	54.8	54.9	56.0	21.4	°C/W	
ψJΤ	Junction-to-top characterization parameter	12.3	17.0	5.2	5.4	1.7	°C/W	
ψJΒ	Junction to baord characterization parameter	43.5	54.4	54.3	55.4	21.5	°C/W	
$\begin{matrix} R_{\theta JC(botto} \\ m \end{matrix}$	Junction-to-case (bottom) thermal resistance	-	-	-	-	9.7	°C/W	

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

<sup>(2)</sup> The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.



#### 6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARA	METER		TEST CONDITIONS		MIN	TYP <sup>(1)</sup>	MAX	UNIT
V <sub>IK</sub>		$V_{CC} = 3 V$ ,	I <sub>I</sub> = -18 mA				-1.2	V
I <sub>I</sub>		$V_{CC} = 3.6 \text{ V},$	$V_I = V_{CC}$ or GND				±1	μΑ
I <sub>off</sub>		$V_{CC} = 0$ ,	$V_I$ or $V_O = 0$ to 3.6 V				15	μΑ
I <sub>CC</sub>		$V_{CC} = 3.6 \text{ V},$	$I_{O} = 0$ ,	$V_I = V_{CC}$ or GND			10	μΑ
$\Delta I_{CC}^{(2)}$	Control	V <sub>CC</sub> = 3.6 V,	One input at 3 V,	Other inputs at V <sub>CC</sub> or GND			300	μΑ
Ci	inputs	V <sub>I</sub> = 3 V or 0				3		pF
(	A port	V 2 V 0 0	<del>0-</del> v			10.5		~F
$C_{io(OFF)}$	B port	$V_{O} = 3 \text{ V or } 0,$	$\overline{OE} = V_{CC}$			5.5		pF
			V 0	I <sub>I</sub> = 64 mA		5	8	
		$V_{CC} = 2.3 \text{ V},$ TYP at $V_{CC} = 2.5 \text{ V}$	$V_1 = 0$	I <sub>I</sub> = 24 mA		5	8	
r <sub>on</sub> (3)		111 at v <sub>CC</sub> = 2.5 v	V <sub>I</sub> = 1.7 V	I <sub>I</sub> = 15 mA		27	40	Ω
I <sub>on</sub> (°)				$I_I = 64 \text{ mA}$		5	7	12
		$V_{CC} = 3 V$	$V_I = 0$	I <sub>I</sub> = 24 mA		5	7	
			V <sub>I</sub> = 2.4 V	I <sub>I</sub> = 15 mA		10	15	

# 6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (See Figure 1)

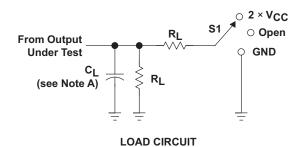
PARAMETER	EDOM (INDUIT)	TO (OUTPUT)	V <sub>CC</sub> = 2.5 ±	0.2 V	$V_{CC} = 3.3 \text{ V}$	± 0.3 V	UNIT
PARAMETER	FROM (INPUT)	TO (OUTPUT)	MIN	MAX	MIN	MAX	UNII
	A or B <sup>(1)</sup>	B or A		0.15		0.25	20
t <sub>pd</sub>	S	A or B	1.8	6.1	1.8	5.3	ns
t <sub>en</sub>	S	A or B	1.7	6.1	1.7	5.3	ns
t <sub>dis</sub>	S	A or B	1	4.8	1	4.5	ns
t <sub>en</sub>	ŌĒ	A or B	1.9	5.6	2	5	ns
t <sub>dis</sub>	ŌĒ	A or B	1	5.5	1.6	5.5	ns

The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

All typical values are at V<sub>CC</sub> = 3.3 V (unless otherwise noted), T<sub>A</sub> = 25°C.
 This is the increase in supply current for each input that is at the specified voltage level, rather than V<sub>CC</sub> or GND.
 Measured by the voltage drop between the A and the B terminals at the indicated current through the switch. On-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

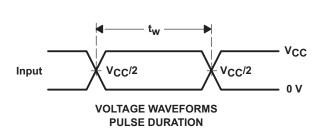


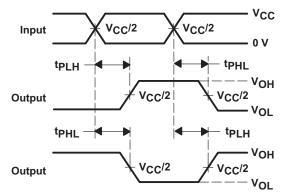
#### 7 Parameter Measurement Information



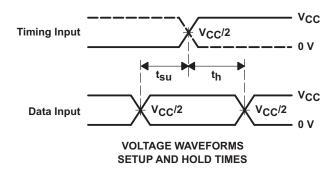
TEST	S1
tPLH/tPHL	Open
tPLZ/tPZL	2 × V <sub>CC</sub>
tPHZ/tPZH	GND

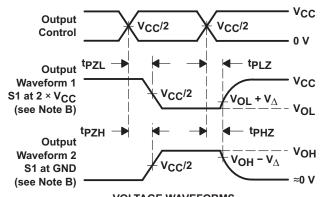
V <sub>CC</sub>	CL	RL	${f v}_{\Delta}$
2.5 V ± 0.2 V	30 pF	<b>500</b> Ω	0.15 V
3.3 V ± 0.3 V	50 pF	<b>500</b> Ω	0.3 V





VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS





VOLTAGE WAVEFORMS ENABLE AND DISABLE TIMES LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C<sub>I</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_Q = 50 \Omega$ ,  $t_f \leq 2$  ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. t<sub>PZL</sub> and t<sub>PZH</sub> are the same as t<sub>en</sub>.
- G. tpLH and tpHL are the same as tpd.
- H. All parameters and waveforms are not applicable to all devices.

Figure 1. Load Circuit and Voltage Waveforms



### 8 Detailed Description

#### 8.1 Overview

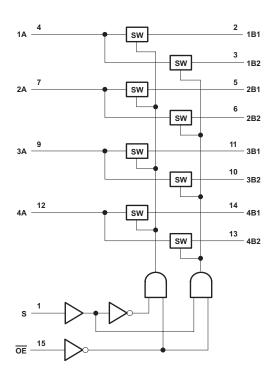
The SN74CBTLV3257 device is a 4-bit 1-of-2 high-speed FET multiplexer and demultiplexer. The low ON-state resistance of the switch allows connections to be made with minimal propagation delay.

The select (S) <u>input</u> controls the data flow. The FET multiplexers and demultiplexers are disabled when the output-enable (OE) input is high.

This device is fully specified for partial-power-down applications using  $I_{off}$ . The  $I_{off}$  feature ensures that damaging current will not backflow through the device when it is powered down. The device has isolation during power off.

To ensure the high-impedance state during power up or power down,  $\overline{OE}$  should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

### 8.2 Functional Block Diagram



#### 8.3 Feature Description

The SN74CBTLV3257 features  $5-\Omega$  switch connection between ports, allowing for low signal loss across the switch. Rail-to-rail switching on data I/O allows for full voltage swing outputs. I<sub>off</sub> supports partial-power-down mode operation, protecting the chip from voltages at output ports when it is not powered on. Latch-up performance exceeds 100 mA per JESD 78, Class II.

#### 8.4 Device Functional Modes

Table 1 shows the functional modes of SN74CBTLV3257.

**Table 1. Function Table** 

INPUTS		FUNCTION
ŌĒ	S	FUNCTION
L	L	A port = B1 port
L	Н	A port = B2 port
Н	X	Disconnect



# 9 Application and Implementation

#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 9.1 Application Information

The SN74CBTLV3257 can be used to multiplex and demultiplex up to 4 channels simultaneously in a 2:1 configuration. The application shown here is a 4-bit bus being multiplexed between two devices. the OE and S pins are used to control the chip from the bus controller. This is a very generic example, and could apply to many situations. If an application requires less than 4 bits, be sure to tie the A side to either high or low on unused channels.

# 9.2 Typical Application

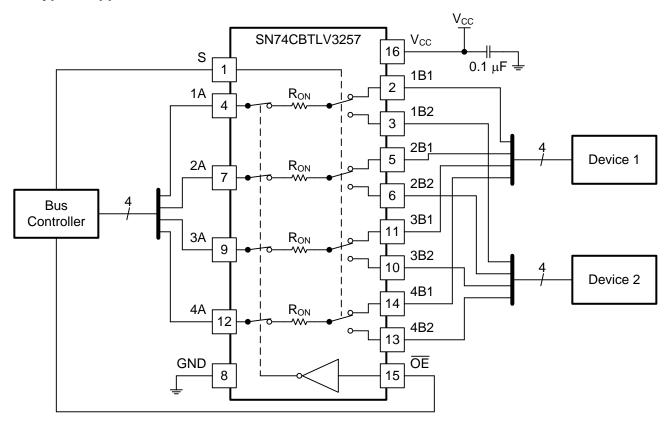


Figure 2. Typical Application of the SN74CBTLV3257

#### 9.2.1 Design Requirements

- Recommended Input Conditions:
  - For specified high and low levels, see V<sub>IH</sub> and V<sub>IL</sub> in Recommended Operating Conditions.
  - Inputs and outputs are overvoltage tolerant slowing them to go as high as 4.6 V at any valid V<sub>CC</sub>.
- 2. Recommended Output Conditions:
  - Load currents should not exceed ±128 mA per channel.
- 3. Frequency Selection Criterion:
  - Maximum frequency tested is 200 MHz.

### **Typical Application (continued)**

 Added trace resistance/capacitance can reduce maximum frequency capability; use layout practices as directed in Layout.

#### 9.2.2 Detailed Design Procedure

The 4-bit bus is connected directly to the 1A, 2A, 3A, and 4A ports (known as the xA port) on the SN74CBTLV3257, which essentially splits it into two busses, coming out of the xB1 and xB2 ports. When S is high, xB2 is the active bus, and when S is low, xB1 is the active bus. This means that Device 2 is connected to the bus controller when S is high, and Device 1 is connected to the bus controller when S is low. This setup is especially useful when two devices are hard coded with the same address and only one bus is available. The OE connection can be used to disconnect all devices from the bus controller if necessary.

The 0.1- $\mu$ F capacitor on  $V_{CC}$  is a decoupling capacitor and should be placed as close as possible to the device.

### 9.2.3 Application Curve

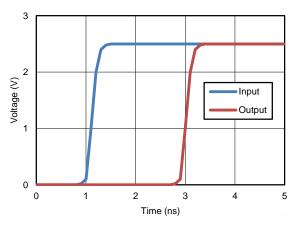


Figure 3. Propagation Delay ( $t_{pd}$ ) Simulation Result at  $V_{CC} = 2.5 \text{ V}$ 

# 10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the *Recommended Operating Conditions* table.

Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- $\mu$ F bypass capacitor is recommended. If multiple pins are labeled  $V_{CC}$ , then a 0.01- $\mu$ F or 0.022- $\mu$ F capacitor is recommended for each  $V_{CC}$  because the  $V_{CC}$  pins are tied together internally. For devices with dual-supply pins operating at different voltages, for example  $V_{CC}$  and  $V_{DD}$ , a 0.1- $\mu$ F bypass capacitor is recommended for each supply pin. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1  $\mu$ F and 1  $\mu$ F are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.



# 11 Layout

# 11.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self–inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. Figure 4 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

#### 11.2 Layout Example

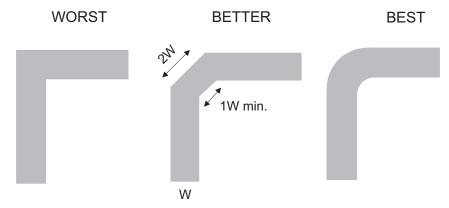


Figure 4. Trace Example



### 12 器件和文档支持

#### 12.1 文档支持

#### 12.1.1 相关文档

请参阅如下相关文档:

- 《慢速或浮点 CMOS 输入的影响》, SCBA004
- 《选择合适的德州仪器 (TI) 信号开关》, SZZA030

#### 12.2 接收文档更新通知

要接收文档更新通知,请导航至 Tl.com.cn 上的器件产品文件夹。单击右上角的通知我进行注册,即可每周接收产品信息更改摘要。有关更改的详细信息,请查看任何已修订文档中包含的修订历史记录。

#### 12.3 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商"按照原样"提供。这些内容并不构成 TI 技术规范,并且不一定反映 TI 的观点;请参阅 TI 的 《使用条款》。

TI E2E™ 在线社区 TI 的工程师对工程师 (E2E) 社区。此社区的创建目的在于促进工程师之间的协作。在 e2e.ti.com 中,您可以咨询问题、分享知识、拓展思路并与同行工程师一道帮助解决问题。

设计支持 71 参考设计支持 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

#### 12.4 商标

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

#### 12.5 静电放电警告



这些装置包含有限的内置 ESD 保护。 存储或装卸时,应将导线一起截短或将装置放置于导电泡棉中,以防止 MOS 门极遭受静电损伤。

#### 12.6 术语表

SLYZ022 — TI 术语表。

这份术语表列出并解释术语、缩写和定义。

# 13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更,恕不另行通知,且不会对此文档进行修订。如需获取此产品说明书的浏览器版本,请查阅左侧的导航栏。





10-Dec-2020

#### **PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
74CBTLV3257PWRE4	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257	Samples
74CBTLV3257PWRG4	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257	Samples
74CBTLV3257RGYRG4	ACTIVE	VQFN	RGY	16	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL257	Samples
SN74CBTLV3257D	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTLV3257	Samples
SN74CBTLV3257DBQR	ACTIVE	SSOP	DBQ	16	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL257	Samples
SN74CBTLV3257DE4	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTLV3257	Samples
SN74CBTLV3257DGVR	ACTIVE	TVSOP	DGV	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257	Samples
SN74CBTLV3257DR	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTLV3257	Samples
SN74CBTLV3257DRE4	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTLV3257	Samples
SN74CBTLV3257PW	ACTIVE	TSSOP	PW	16	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257	Samples
SN74CBTLV3257PWE4	ACTIVE	TSSOP	PW	16	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257	Samples
SN74CBTLV3257PWG4	ACTIVE	TSSOP	PW	16	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL257	Samples
SN74CBTLV3257PWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 85	CL257	Samples
SN74CBTLV3257RGYR	ACTIVE	VQFN	RGY	16	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL257	Samples
SN74CBTLV3257RSVR	ACTIVE	UQFN	RSV	16	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ZTR	Samples

<sup>(1)</sup> The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW**: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE**: TI has discontinued the production of the device.



# PACKAGE OPTION ADDENDUM

10-Dec-2020

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 16-Feb-2022

# TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

# QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

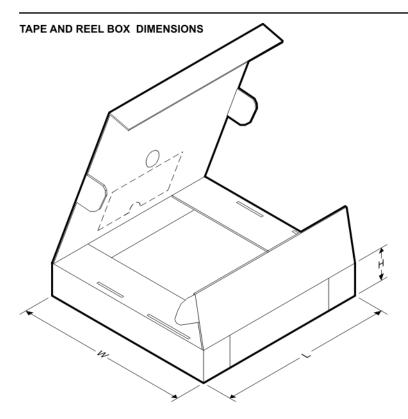


#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74CBTLV3257PWRG4	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CBTLV3257DBQR	SSOP	DBQ	16	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
SN74CBTLV3257DGVR	TVSOP	DGV	16	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74CBTLV3257DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN74CBTLV3257PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CBTLV3257PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CBTLV3257RGYR	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1
SN74CBTLV3257RSVR	UQFN	RSV	16	3000	180.0	13.2	2.1	2.9	0.75	4.0	12.0	Q1



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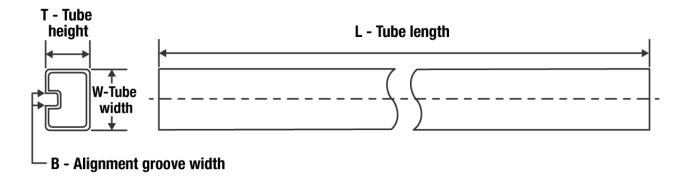
\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74CBTLV3257PWRG4	TSSOP	PW	16	2000	367.0	367.0	35.0
SN74CBTLV3257DBQR	SSOP	DBQ	16	2500	340.5	338.1	20.6
SN74CBTLV3257DGVR	TVSOP	DGV	16	2000	367.0	367.0	35.0
SN74CBTLV3257DR	SOIC	D	16	2500	340.5	336.1	32.0
SN74CBTLV3257PWR	TSSOP	PW	16	2000	367.0	367.0	35.0
SN74CBTLV3257PWR	TSSOP	PW	16	2000	364.0	364.0	27.0
SN74CBTLV3257RGYR	VQFN	RGY	16	3000	367.0	367.0	35.0
SN74CBTLV3257RSVR	UQFN	RSV	16	3000	180.0	180.0	30.0

# PACKAGE MATERIALS INFORMATION

www.ti.com 16-Feb-2022

# **TUBE**



\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74CBTLV3257D	D	SOIC	16	40	507	8	3940	4.32
SN74CBTLV3257DE4	D	SOIC	16	40	507	8	3940	4.32
SN74CBTLV3257PW	PW	TSSOP	16	90	530	10.2	3600	3.5
SN74CBTLV3257PWE4	PW	TSSOP	16	90	530	10.2	3600	3.5
SN74CBTLV3257PWG4	PW	TSSOP	16	90	530	10.2	3600	3.5

# D (R-PDS0-G16)

# PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.



# D (R-PDSO-G16)

# PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





SMALL OUTLINE PACKAGE



- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



# DGV (R-PDSO-G\*\*)

# 24 PINS SHOWN

#### **PLASTIC SMALL-OUTLINE**



NOTES: A. All linear dimensions are in millimeters.

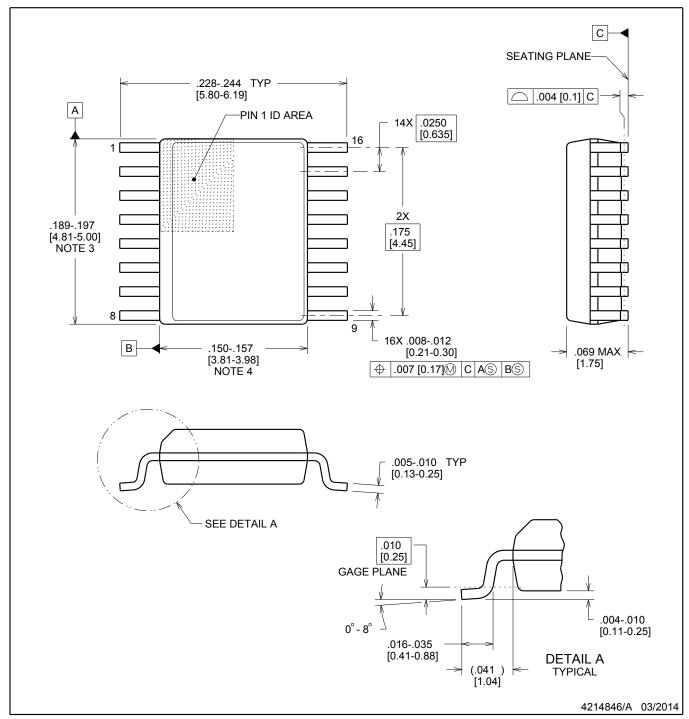
B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.

D. Falls within JEDEC: 24/48 Pins – MO-153 14/16/20/56 Pins – MO-194



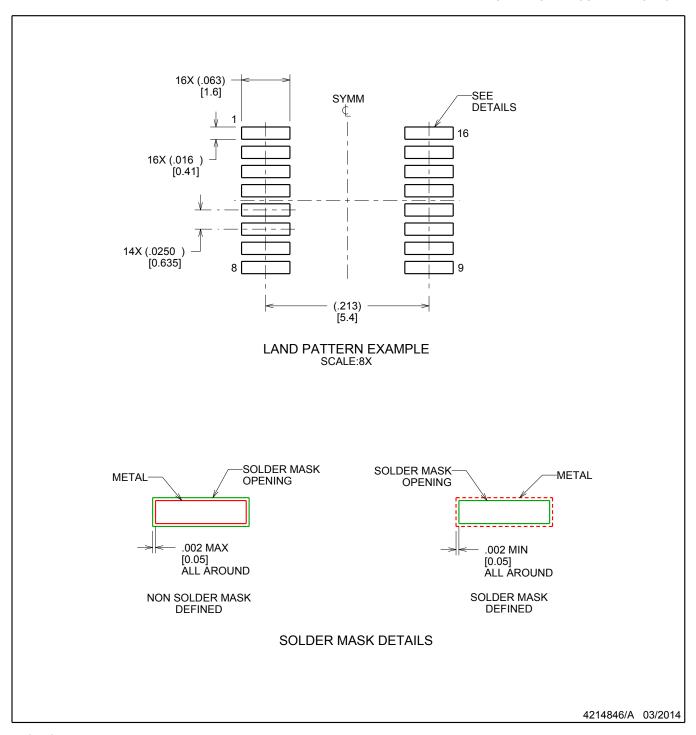
SHRINK SMALL-OUTLINE PACKAGE



- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 inch, per side.
- 4. This dimension does not include interlead flash.5. Reference JEDEC registration MO-137, variation AB.



SHRINK SMALL-OUTLINE PACKAGE



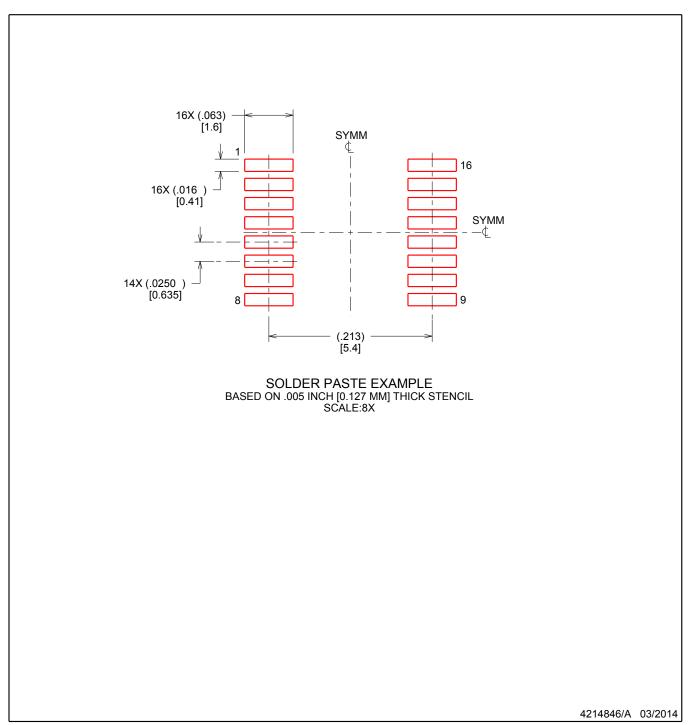
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



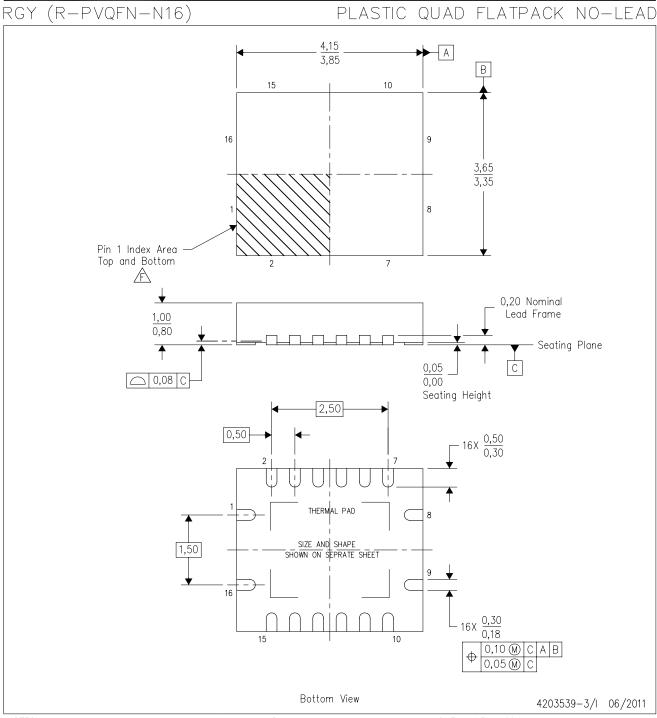
SHRINK SMALL-OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. QFN (Quad Flatpack No-Lead) package configuration.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.
- G. Package complies to JEDEC MO-241 variation BA.



# RGY (R-PVQFN-N16)

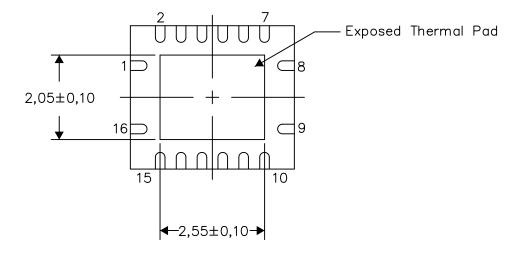
# PLASTIC QUAD FLATPACK NO-LEAD

#### THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

Exposed Thermal Pad Dimensions

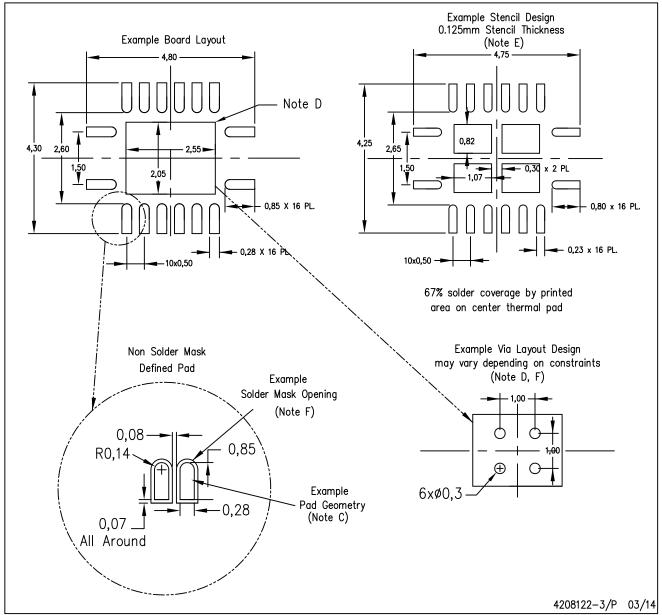
4206353-3/P 03/14

NOTE: All linear dimensions are in millimeters



# RGY (R-PVQFN-N16)

# PLASTIC QUAD FLATPACK NO-LEAD

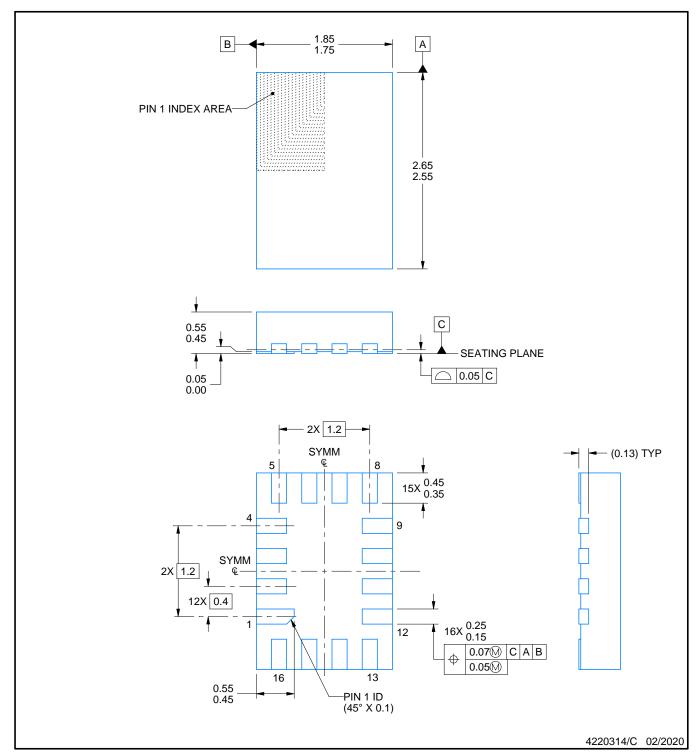


- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat—Pack QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <a href="https://www.ti.com">http://www.ti.com</a>.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.





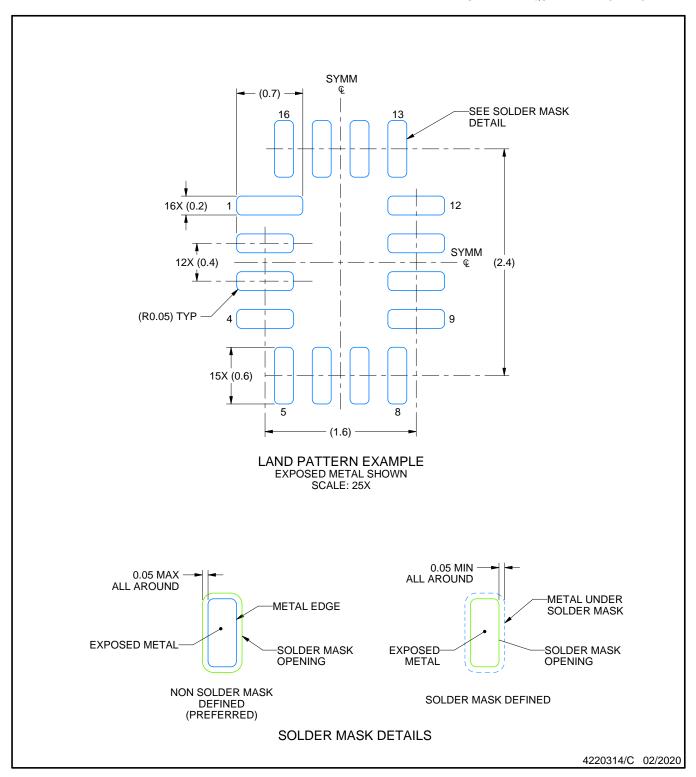
ULTRA THIN QUAD FLATPACK - NO LEAD



- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
   This drawing is subject to change without notice.



ULTRA THIN QUAD FLATPACK - NO LEAD

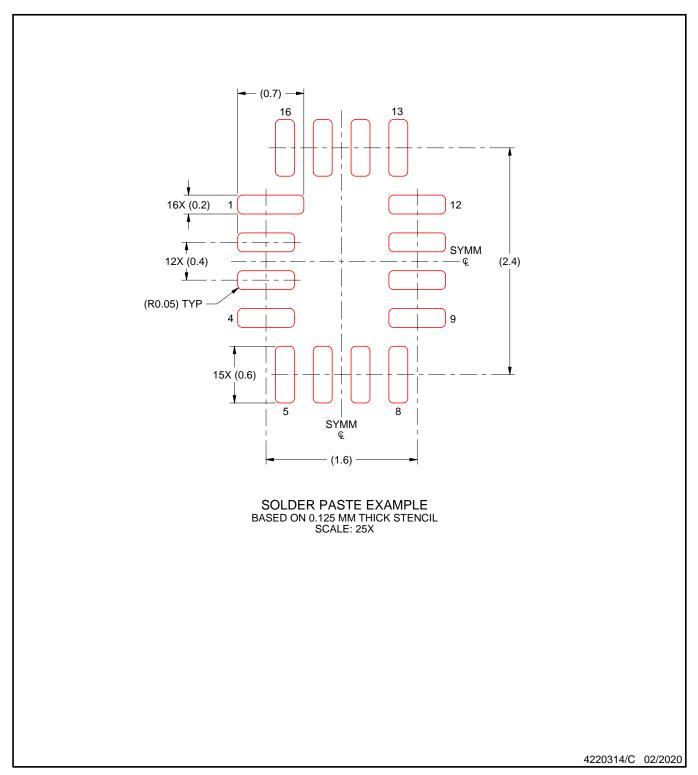


NOTES: (continued)

3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).



ULTRA THIN QUAD FLATPACK - NO LEAD



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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